imall

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Taiwan Semiconductor

Dual Common Cathode Schottky Rectifier

FEATURES

- Low power loss, high efficiency
- Guardring for overvoltage protection
- High surge current capability
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

MECHANICAL DATA

Case: TO-220AB

Molding compound, UL flammability classification rating 94V-0 Base P/N with suffix "G" on packing code - halogen-free

Base P/N with prefix "H" on packing code - AEC-Q101 qualified

Terminal: Matte tin plated leads, solderable per JESD22-B102

Meet JESD 201 class 1A whisker test,

with prefix "H" on packing code meet JESD 201 class 2 whisker test **Polarity:** As marked

Mounting torque: 5 in-lbs maximum

Weight: 1.9 g (approximately)











PARAMETER	SYMBOL	MBR20	L100CT	MBR20	L120CT	UNIT
Maximum repetitive peak reverse voltage	V _{RRM}	100		120		V
Maximum RMS voltage	V _{RMS}	70		84		V
Maximum DC blocking voltage	V _{DC}	100		120		V
Maximum average forward rectified current	I _{F(AV)}	20			Α	
Peak repetitive forward current (Rated VR, Square Wave, 20KHz)	I _{FRM}	20			А	
Peak forward surge current, 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}	150			А	
Peak repetitive reverse surge current (Note 1)	I _{RRM}	1			А	
Maximum instantaneous forward voltage (Note 2)		TYP	MAX	TYP	MAX	v
I _F = 10A, T _J =25℃		0.72	0.75	0.78	0.83	
₌= 10A, Tյ=125℃ ₌= 20A, Tյ=25℃	V _F	0.58	0.68	0.63	0.72	
		0.81	0.85	0.86	0.90	
I _F = 20A, T _J =125℃		0.67	0.75	0.73	0.80	
Maximum reverse current @ rated VR		TYP	MAX	TYP	MAX	
T _J =25 ℃	I _R	1.10	20	1.00	20	μA
T _J =125 ℃		1.20	15	1.40	10	mA
Voltage rate of change (Rated V _R)	dV/dt	10000			V/µs	
Typical thermal resistance	R _{eJC}	2.8 3.0		°C/W		
Operating junction temperature range	TJ	- 55 to +150			°C	
Storage temperature range	T _{STG}	- 55 to +150				°C

Note 1: tp = 2.0 µs, 1.0KHz

Note 2: Pulse test with PW=300µs, 1% duty cycle



MBR20L100CT thru MBR20L120CT

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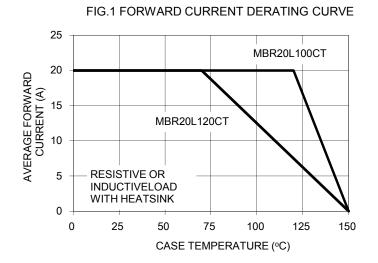
ORDERING INFORMATION						
PART NO.	AEC-Q101 QUALIFIED	PACKING CODE	GREEN COMPOUND CODE	PACKAGE	PACKING	
MBR20L1xxCT	Prefix "H"	C0	Suffix "G"	TO-220AB	50 / Tube	
Note 1: "yet" defines yoltage from 100\/ (MPP20I 100CT) to 120\/ (MPP20I 120CT)						

Note 1: "xx" defines voltage from 100V (MBR20L100CT) to 120V (MBR20L120CT)

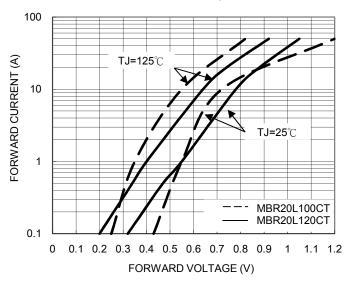
EXAMPLE						
PREFERRED P/N	PART NO.	AEC-Q101 QUALIFIED	PACKING CODE	GREEN COMPOUND CODE	DESCRIPTION	
MBR20L100CT C0	MBR20L100CT		C0			
MBR20L100CT C0G	MBR20L100CT		C0	G	Green compound	
MBR20L100CTHC0	MBR20L100CT	Н	C0		AEC-Q101 qualified	

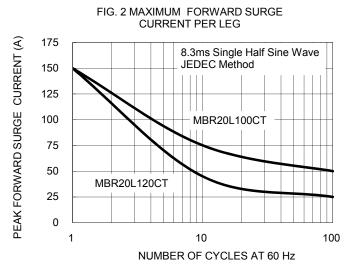
RATINGS AND CHARACTERISTICS CURVES

(TA=25 $^{\circ}$ C unless otherwise noted)

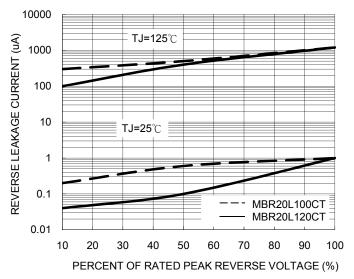








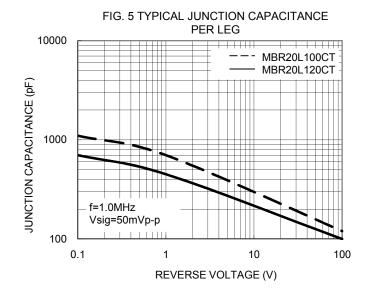


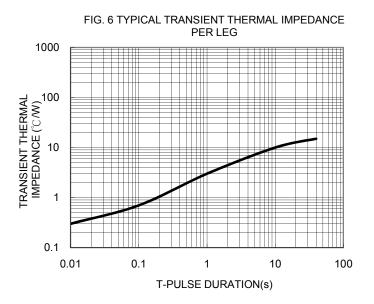




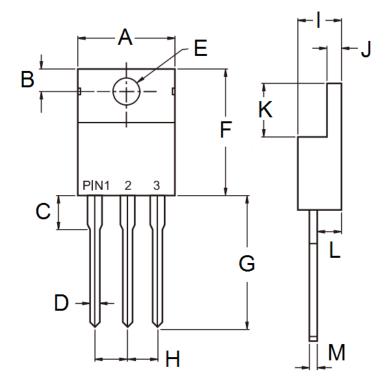
MBR20L100CT thru MBR20L120CT

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PACKAGE OUTLINE DIMENSIONS



P/N

YWW

G

F

DIM.	Unit	(mm)	Unit (inch)		
DIM.	Min	Min Max		Max	
А	-	10.50	-	0.413	
В	2.62	3.44	0.103	0.135	
С	2.80	4.20	0.110	0.165	
D	0.68	0.94	0.027	0.037	
E	3.54	4.00	0.139	0.157	
F	14.60	16.00	0.575	0.630	
G	13.19	14.79	0.519	0.582	
Н	2.41	2.67	0.095	0.105	
I	4.42	4.76	0.174	0.187	
J	1.14	1.40	0.045	0.055	
K	5.84	6.86	0.230	0.270	
L	2.20	2.80	0.087	0.110	
М	0.35	0.64	0.014	0.025	

MARKING DIAGRAM



- = Specific Device Code = Green Compound
 - = Date Code
 - = Factory Code



Taiwan Semiconductor

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